



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SK3745LS — High-Voltage, High-Speed Switching Applications

N-Channel Silicon MOSFET

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching
- High reliability (Adoption of HVP process)
- Micaless package facilitating mounting
- Avalanche resistance guarantee

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1500	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D [*]		2	A
Drain Current (Pulse)	I _{DP}		4	A
Allowable Power Dissipation	P _D		2.0	W
		T _c =25°C	35	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		41	mJ
Avalanche Current *2	I _{AV}		2	A

*Shows chip capability

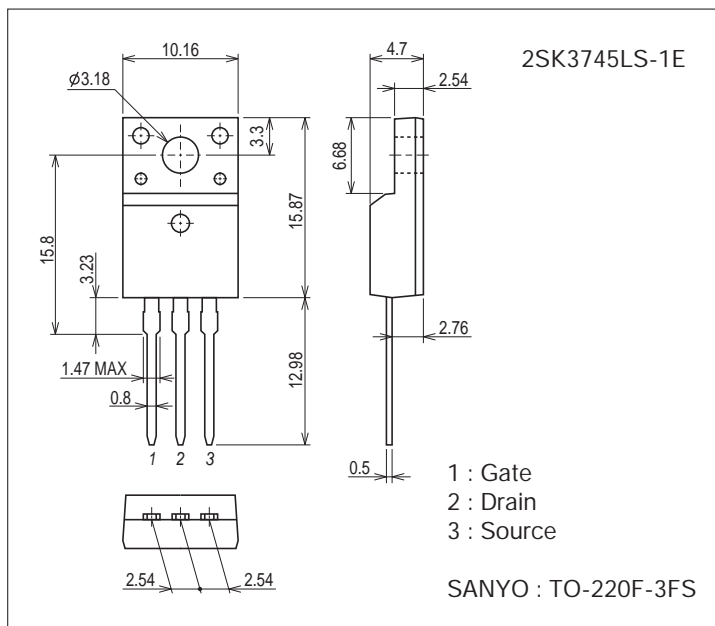
*1 V_{DD}=50V, L=20mH, I_{AV}=2A (Fig.1)

*2 L≤20mH, single pulse

Package Dimensions

unit : mm (typ)

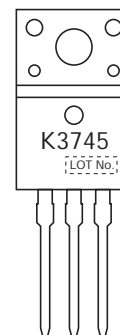
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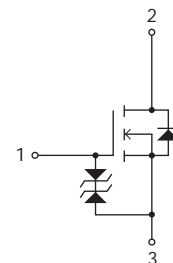
Product & Package Information

- Package : TO-220F-3FS
- JEITA, JEDEC : SC-67
- Minimum Packing Quantity : 50 pcs./magazine

Marking



Electrical Connection



2SK3745LS

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
			min	typ	max		
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	1500			V	
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V$			100	μA	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=16V, V_{DS}=0V$			± 10	μA	
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	2.5		3.5	V	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=20V, I_D=1A$	0.7	1.4		S	
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=1A, V_{GS}=10V$		10	13	Ω	
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		380		pF	
Output Capacitance	C_{oss}				70		pF
Reverse Transfer Capacitance	C_{rss}				40		pF
Turn-ON Delay Time	$t_{d(on)}$	See Fig.2		12		ns	
Rise Time	t_r				37		ns
Turn-OFF Delay Time	$t_{d(off)}$				152		ns
Fall Time	t_f				59		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		37.5		nC	
Gate-to-Source Charge	Q_{gs}				2.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}				20		nC
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V$		0.88	1.2	V	

Fig.1 Avalanche Resistance Test Circuit

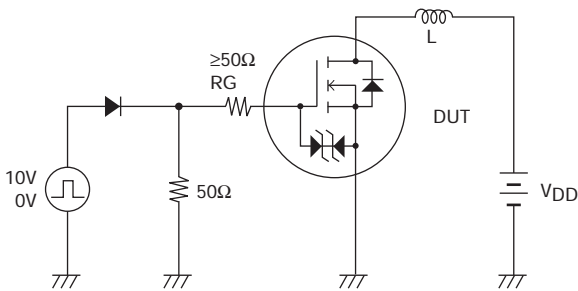
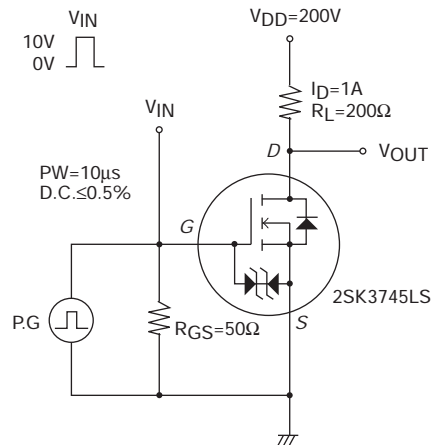


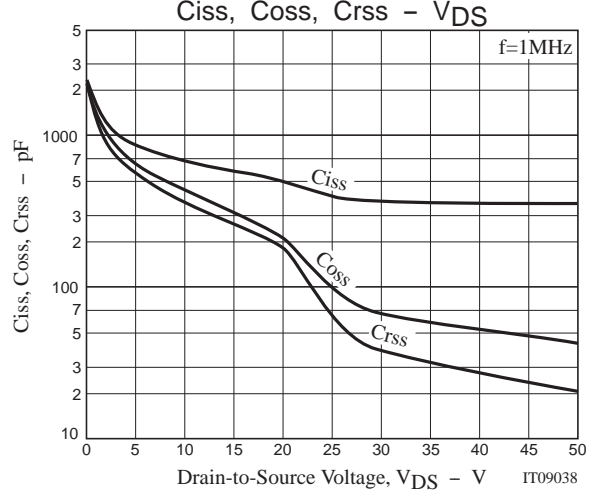
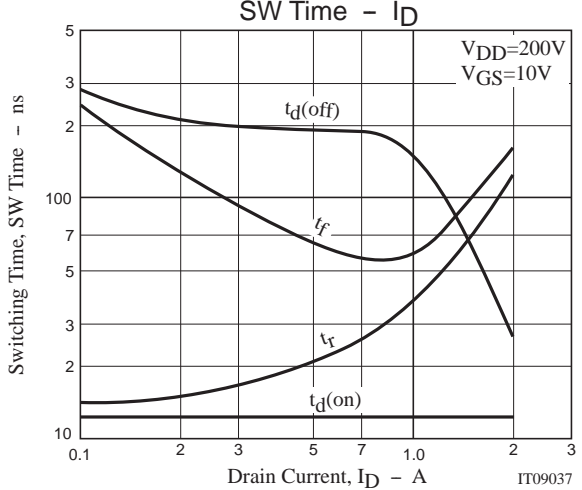
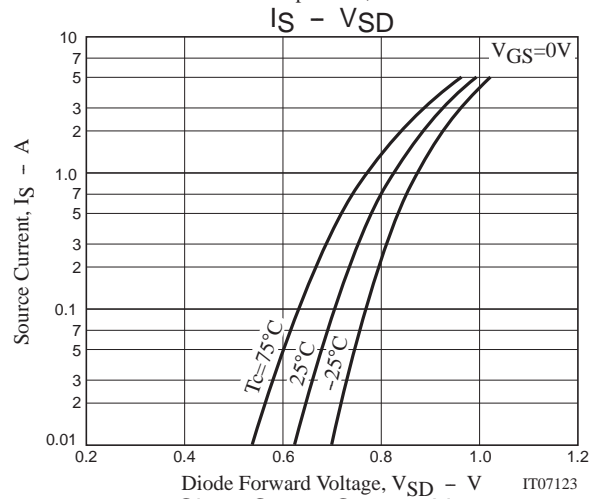
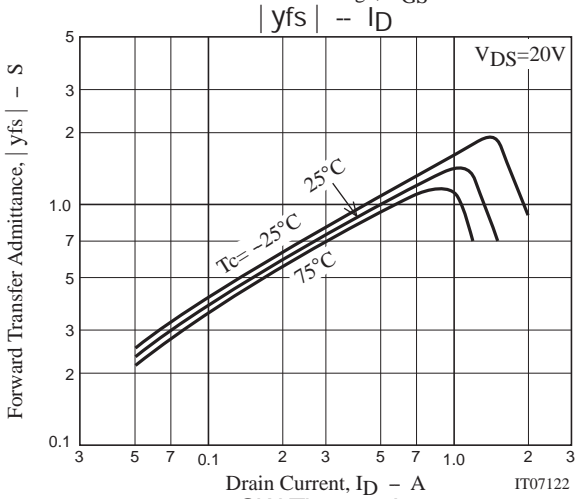
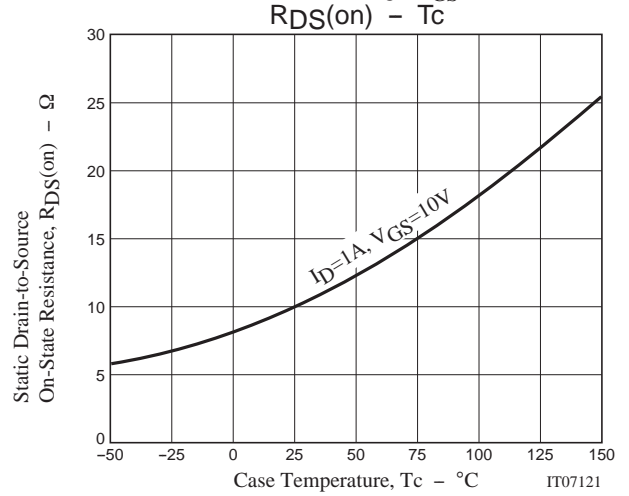
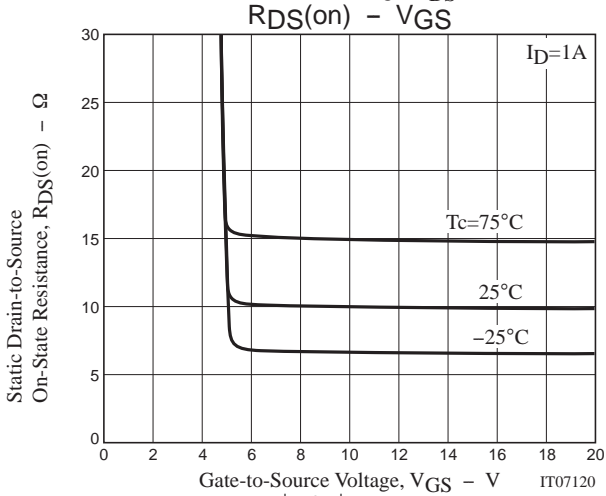
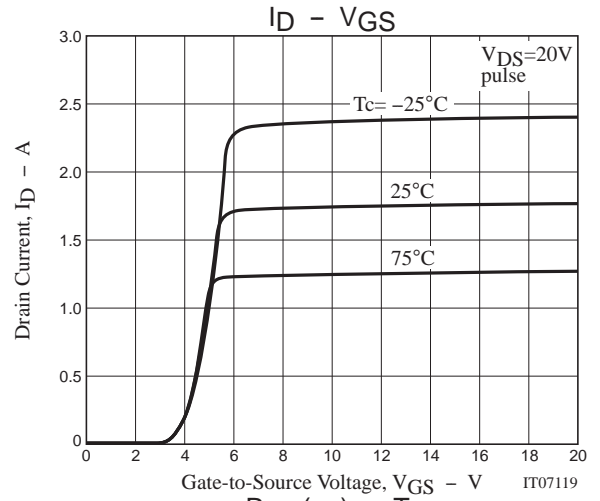
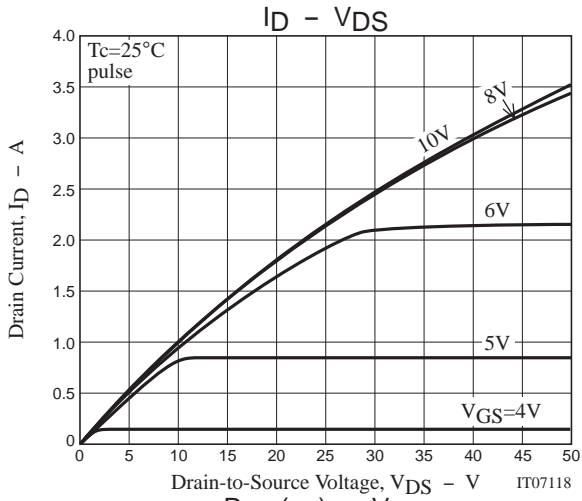
Fig.2 Switching Time Test Circuit



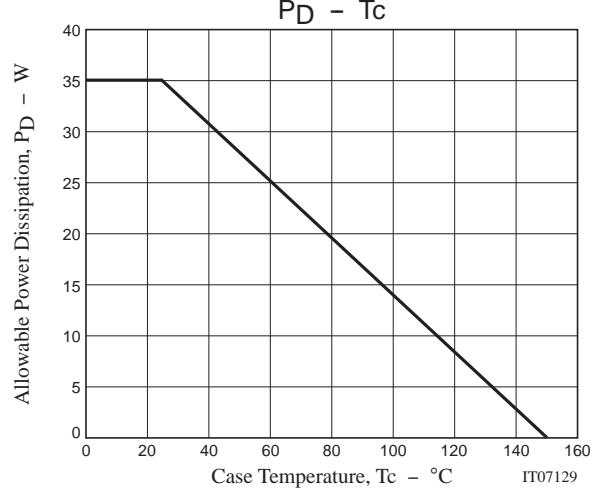
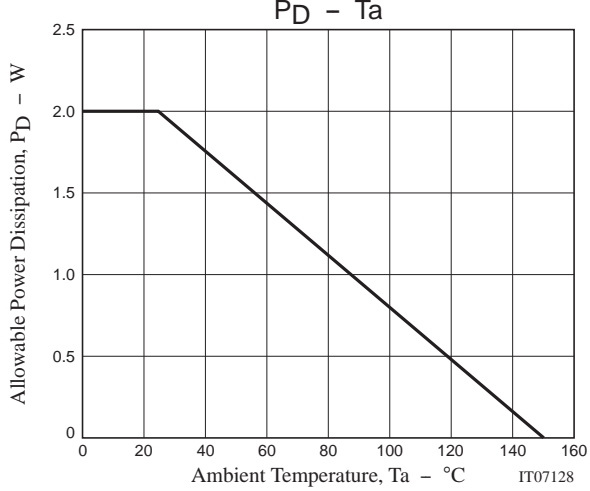
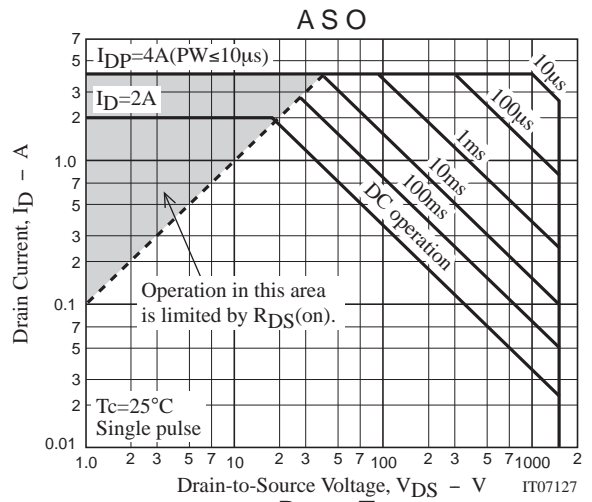
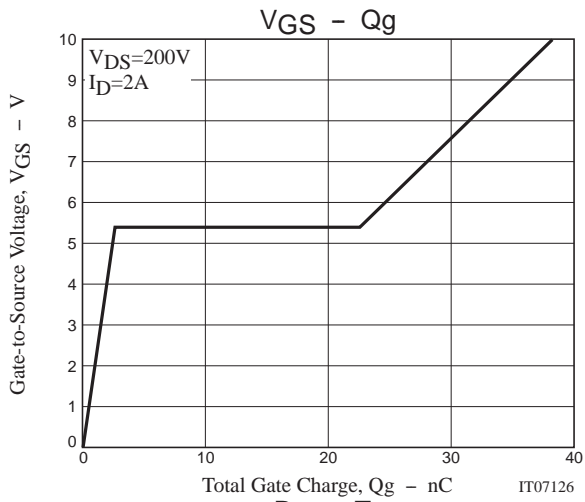
Ordering Information

Device	Package	Shipping	memo
2SK3745LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free

2SK3745LS



2SK3745LS



2SK3745LS

Magazine Specification

2SK3745LS-1E

1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (pcs)			Packing format	
		Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3FS	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

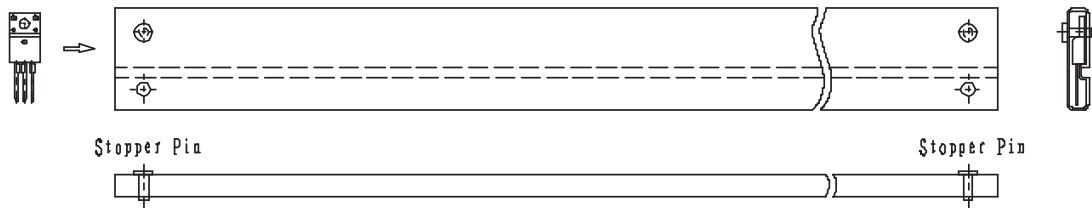
2. Magazine dimensions

(unit:mm)

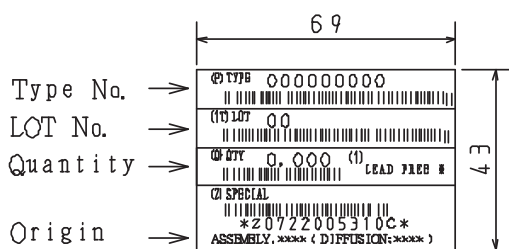


Tolerance=±0.3mm
 Thickness=0.7±0.2mm
 Length =532.5±2mm
 Material =PVC (Antistatic treatment)

3. Storage method to magazine

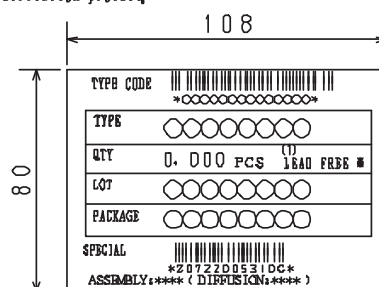


4. Inner box label (unit:mm)



5. Outer box label (unit:mm)

It is a label at the time of factory shipments.
 The form of a label may change in physical
 distribution process.



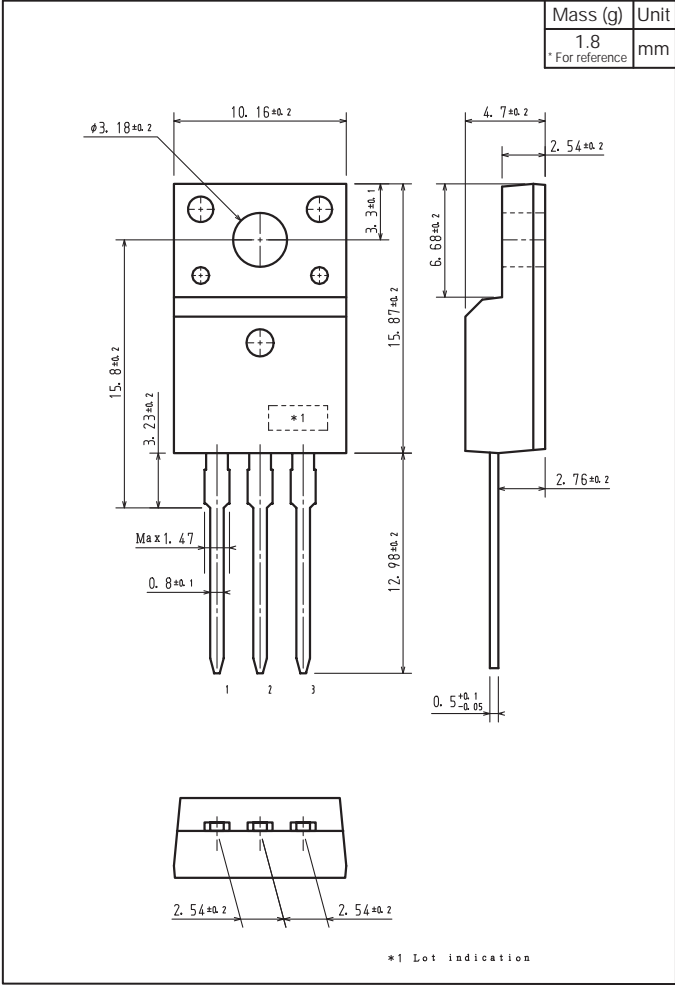
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

2SK3745LS

Outline Drawing
2SK3745LS-1E



Note on usage : Since the 2SK3745LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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